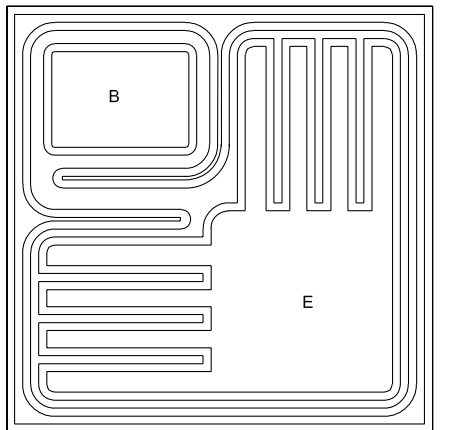


**PROCESS DETAILS**

Process	EPITAXIAL BASE
Die Size	80 X 80 MILS
Die Thickness	8 MILS
Base Bonding Pad Area	18 X 27 MILS
Emitter Bonding Pad Area	34 X 34 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Pd/Ag (20,000Å)

**GEOMETRY**



BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

1,445

**PRINCIPAL DEVICE TYPES**

CZT122  
CJD122

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
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